

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CQ220-6BS
CQ220-6DS
CQ220-6MS
CQ220-6NS

6.0 AMP TRIAC
200 THRU 800 VOLTS

JEDEC TO-220AB CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CQ220-6BS series type is an Epoxy Molded Silicon Triac designed for full wave AC control applications featuring gate triggering in all four (4) quadrants.

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

	SYMBOL	CQ220 -6BS	CQ220 -6DS	CQ220 -6MS	CQ220 -6NS	UNITS
Peak Repetitive Off-State Voltage	V _{DRM}	200	400	600	800	V
RMS On-State Current (T _C = 90°C)	I _{T(RMS)}		6.0			A
Peak One Cycle Surge (t = 10ms)	I _{TSM}		60			A
I ² t Value for Fusing (t = 10ms)	I ² t		18			A ² s
Peak Gate Power (tp = 10μs)	P _{GM}		40			W
Average Gate Power Dissipation	P _{G(AV)}		1.0			W
Peak Gate Current (tp = 10μs)	I _{GM}		4.0			A
Peak Gate Voltage (tp = 10μs)	V _{GM}		16			V
Critical Rate of Rise of On-State Current						
Repetitive (F = 50Hz)	di/dt		10			A/μs
Storage Temperature	T _{stg}		-40 to +150			°C
Junction Temperature	T _J		-40 to +110			°C
Thermal Resistance	θ _{J-A}		60			°C/W
Thermal Resistance	θ _{J-C}		3.2			°C/W

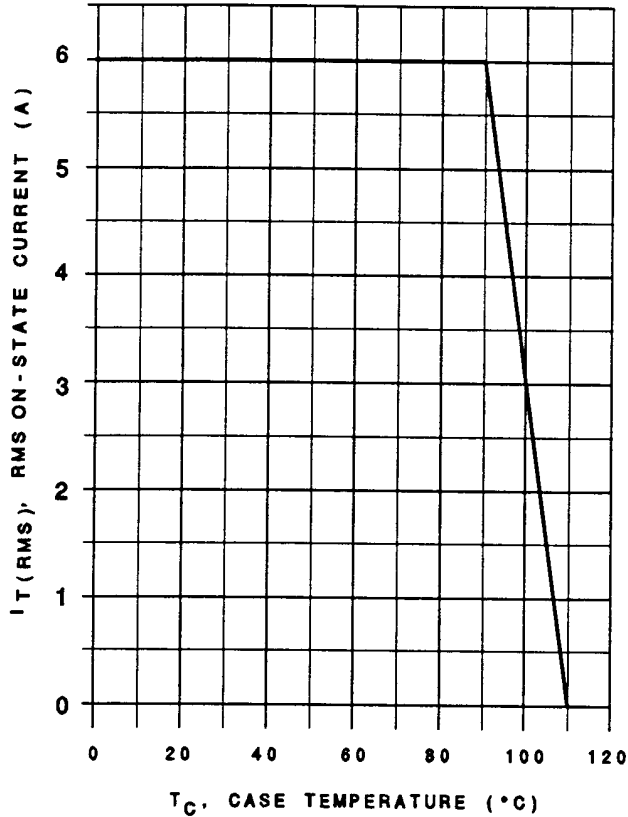
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{DRM}	Rated V _{DRM}			0.01	mA
I _{DRM}	Rated V _{DRM} , T _C = 110°C			0.75	mA
I _{GT}	V _D = 12V, R _L = 33Ω, QUAD I,II,III			5.0	mA
I _{GT}	V _D = 12V, R _L = 33Ω, QUAD IV			10	mA
I _H	I _T = 100mA			15	mA
V _{GT}	V _D = 12V, R _L = 33Ω, QUAD I,II,III,IV			1.50	V
V _{TM}	I _{TM} = 8.5A, tp = 10ms			1.65	V
dv/dt	V _D = 2/3 V _{DRM} , R _{GK} = ∞, T _C = 110°C		10		V/μs

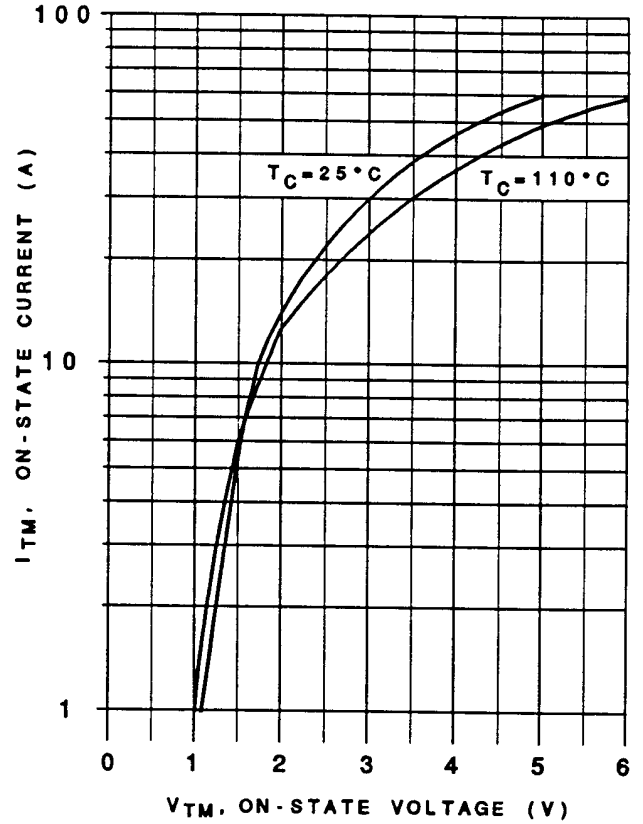
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CQ220-6BS SERIES RATING AND CHARACTERISTIC CURVES

RMS ON-STATE CURRENT vs. CASE TEMPERATURE



MAXIMUM ON-STATE CHARACTERISTICS



MECHANICAL DIMENSIONS

All Dimensions in inches (mm).

